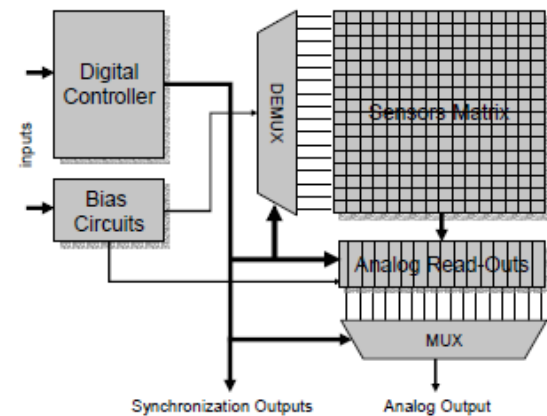


CMOS–SOI–MEMS Transistor (TeraMOS) for Terahertz Imaging

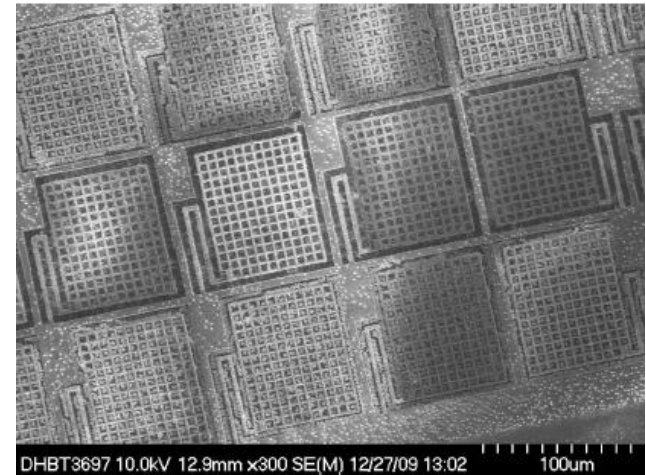
D. Corcos, D. Goren, Y. Nemirovsky

- ▶ Research Goal: to design a passive imager for the THz waves
- ▶ Specifications:
 - Wavelength 200–600 μm (range 0.5–1.5 THz)
 - Video frame rate \sim 20–60 ms
 - High sensitivity: NETD < 1K
 - Monolithic FPA and read-out design



CMOS-SOI-MEMS Transistor (TeraMOS) for Terahertz Imaging

- ▶ Proposed sensing element:
a suspended MOS transistor, thermally isolated by micromachining (MEMS), and operated in sub-threshold; EM coupling achieved with direct absorber or integrated antenna
- ▶ Expected performance:
 - NEP=5pW, NETD=1K
 - TCC=4.5 %/K (measured)
with 0.02 %/K² variation
 - absorption efficiency $\eta=90\%$
- ▶ Research program for 2010:
 - Optical characterization of the first design
 - Production of an optimized device



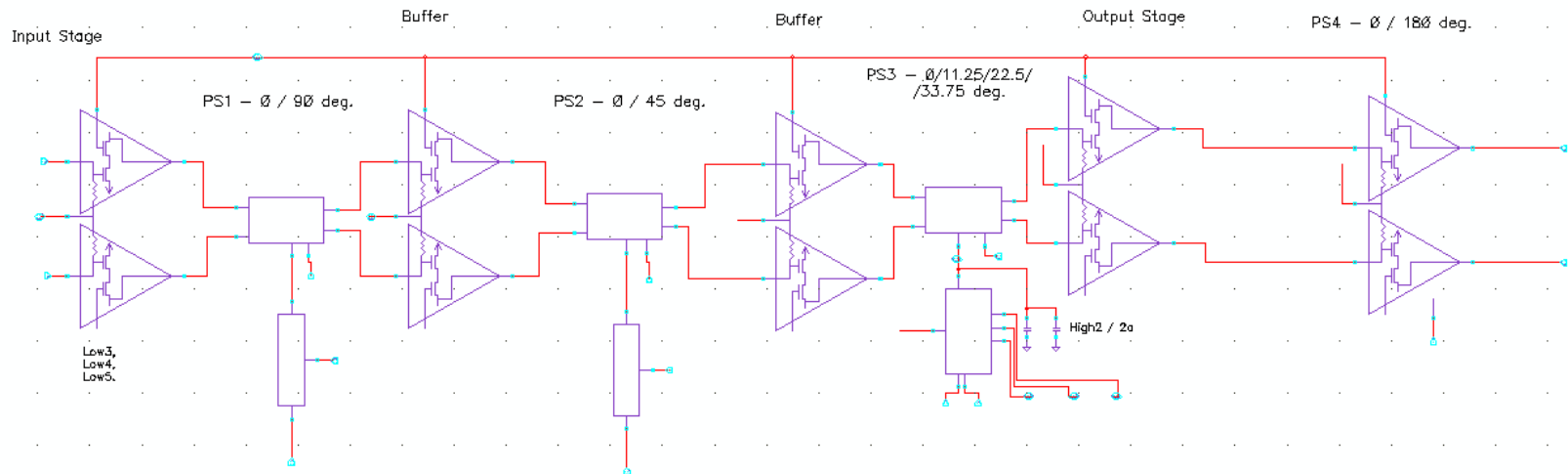
Design of CMOS Phase Shifter,

Gal Segev, I. Brouk, Y. Nemirowsky

► Specifications:

- 360° coverage with 5 bits
- working frequency: 12.5GHz
- Bandwidth: 1GHz

► Main goal: design on Tower's process – 0.18 μ m



Achievements and Broadcast

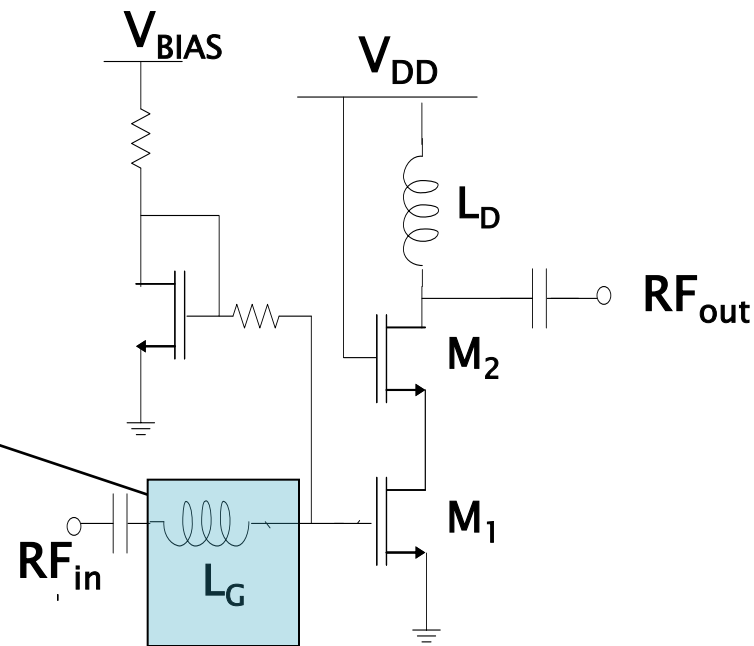
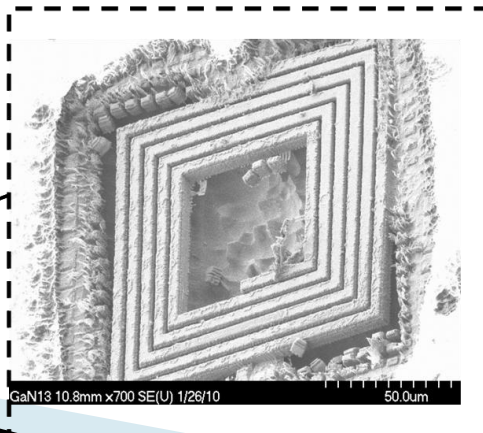
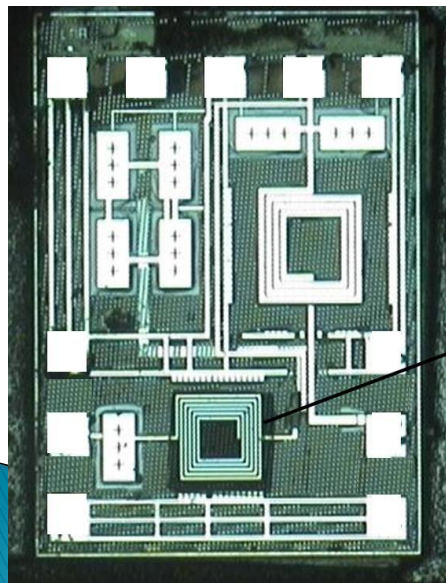
- ▶ Results of our design:
 - Area: 3X3 mm²
 - Losses: -0.3 dB
 - Gain Variation: ± 0.4 dB
 - Phase Error: $< 0.4^\circ$
 - Temperature range: $-20^\circ \div 80^\circ$
 - Ability to re-calibrate the PS after production.

- ▶ PS is now on fabrication.
Measurements will be held on its return.

A CMOS Low Noise Amplifier with Integrated Front-Side Micromachined Inductor

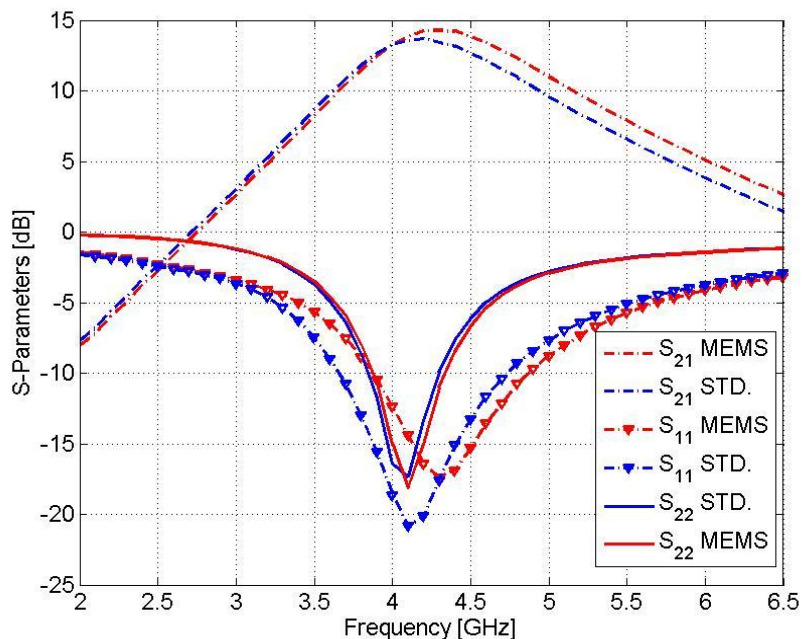
R. Ben-Yishay, S. Stolyarova and Y. Nemirovsky

- ▶ RFIC inductors performance are improved by a selective removal of surrounding silicon and oxide.
- ▶ **Main goal:** Study of post-processing effects on active CMOS circuit performance

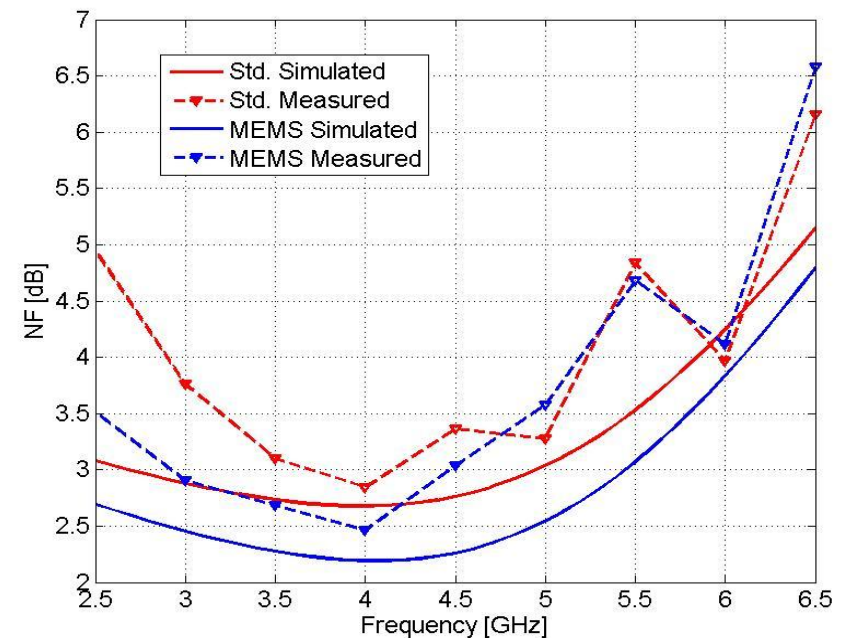


- ▶ Case study – 4GHz CMOS LNA fabricated in Tower 0.18 μm
- ▶ Low cost CMOS compatible post processing technique was applied on the inductor in the input matching network.
- ▶ Measurement results:
 - NF improvement of 0.5dB
 - Gain enhancement of 1 dB
- ▶ Paper submitted to IEEE Electron Devices Letters

Measured S-parameters



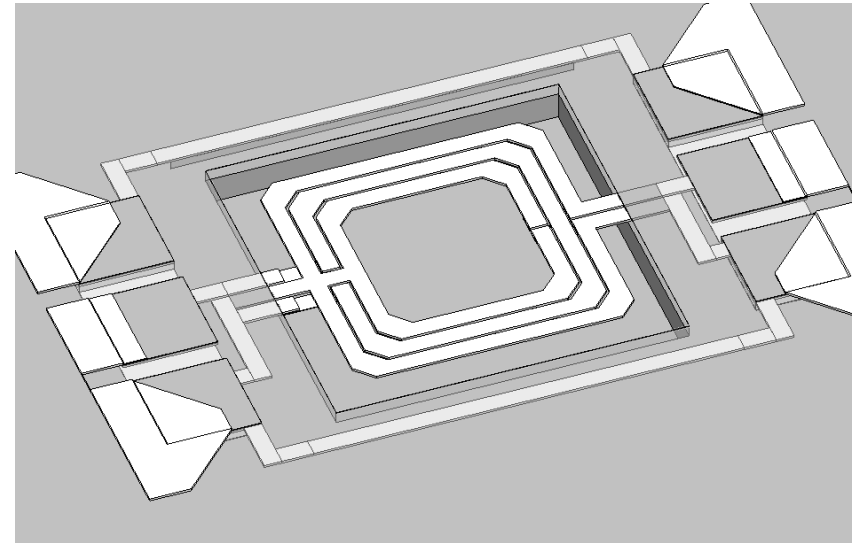
Measured & Simulated Noise Figure



High Performance MEMS 0.18 μm RF-CMOS Transformers

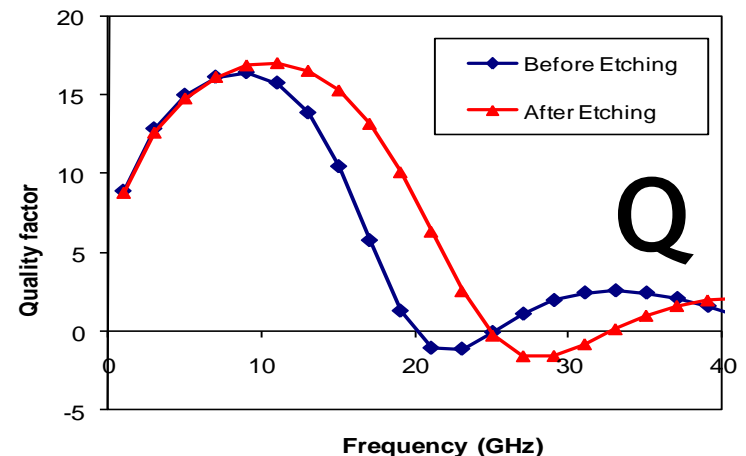
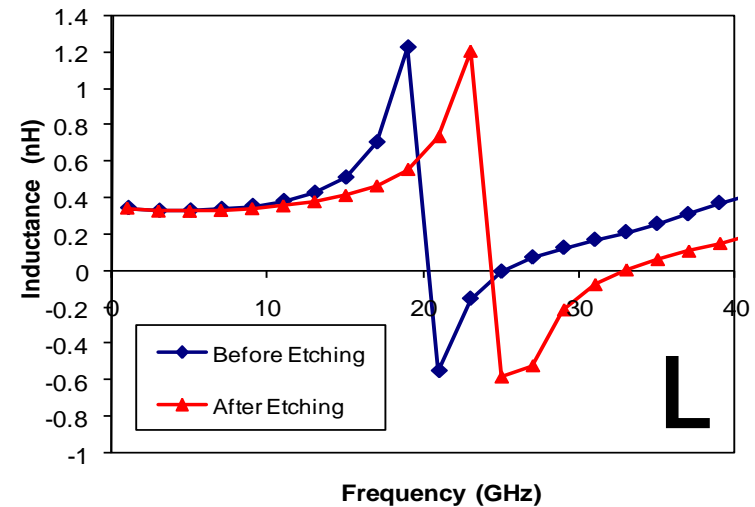
Shlomo Katz, I. Brouk, S. Stolyarova, S. Shapira, Y. Nemirovsky

- ▶ **Background:**
 - Inductor/transformer parasitic elements: C, R
 - Parasitics cause self-resonance and limit Q
 - Removing oxide/substrate material decreases parasitics
- ▶ **Main goal: Improve transformer performance with MEMS post-processing**



Results and Achievements

- ▶ Results of our design:
 - Peak Q and self-resonant frequencies increased by over 20%
 - Insertion loss and cross-talk reduced
- ▶ Results pictured are from HFSS simulations. Devices recently returned from fabrication; measurements will be performed after post-processing .



FOX: Fast on-chip Interconnect

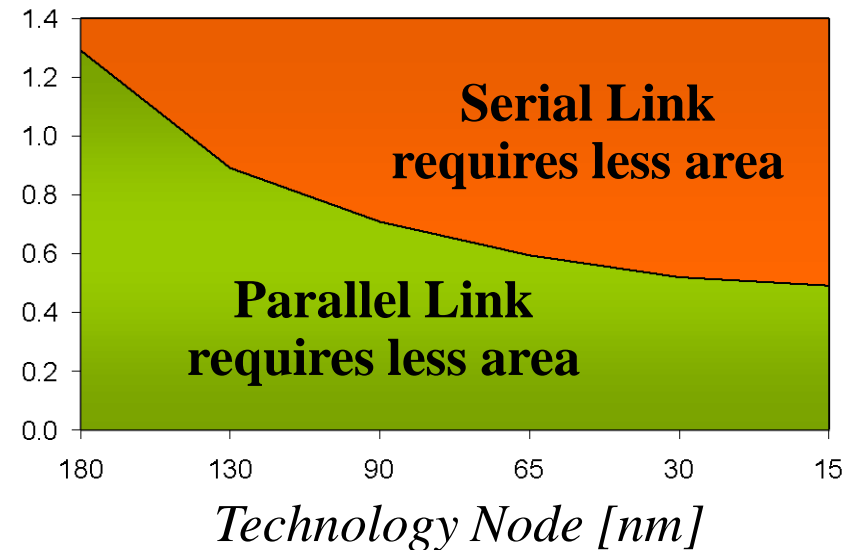
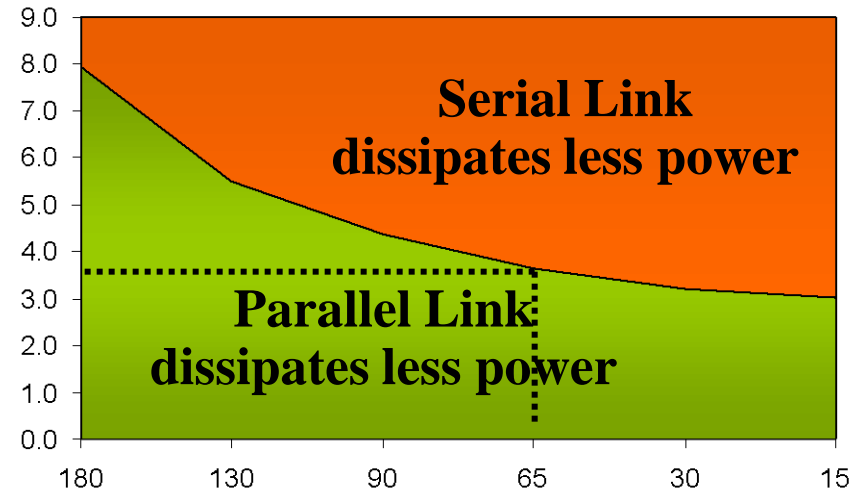
*Very high speed on-chip serial
interconnect*

Dr. Reuven Dobkin
Prof. Ran Ginosar
Prof. Avinoam Kolodny

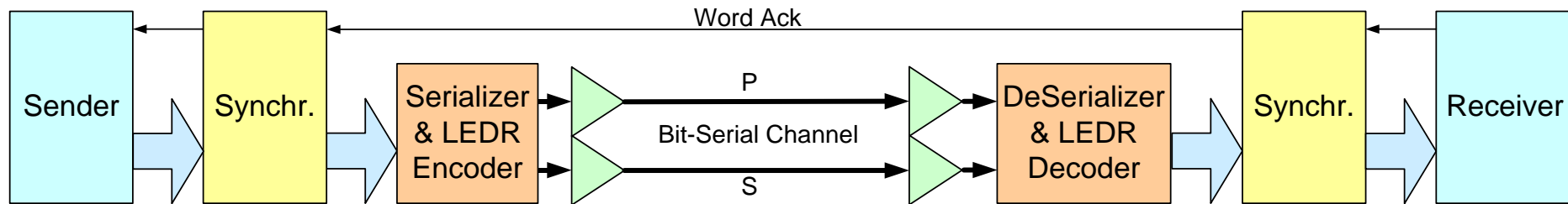
Serial Link Employment Benefits

- ▶ Why Serial Link?
 - Less interconnect area
 - Less routing congestion
- ▶ Less coupling
 - Less power (depends on range)
- ▶ The relative improvement grows with technology scaling

Link Length [mm]



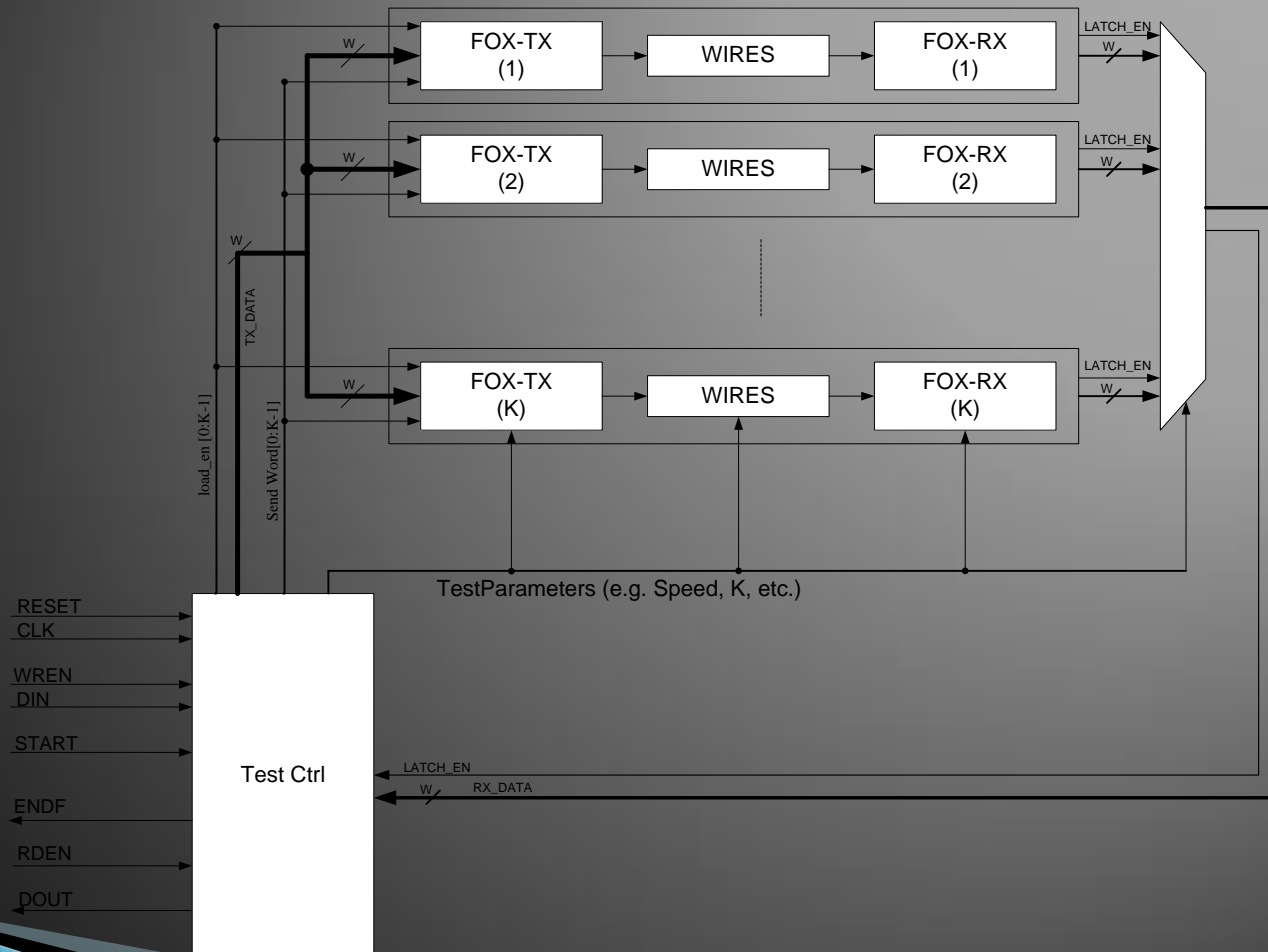
Serial Link Structure



- ▶ Transition signaling instead of sampling: two-phase NRZ Level Encoded Dual Rail (LEDR) asynchronous protocol, a.k.a. data-strobe (DS)
- ▶ Acknowledge per word instead of per bit
- ▶ Wave-pipelining over channel
- ▶ Differential encoding (DS-DE, IEEE1355-95)
- ▶ Low-latency synchronizers
- ▶ **Single gate delay data cycle (faster than anyone else)**
 - 67Gbps @ HP65nm

FOX test-chip (fabrication in 2010)

Link Architecture (only one is active per a time)



FOX: Fast on-chip Interconnect

*High speed, Current mode serial
interconnect*

Danniel Nahmanny
Prof. Ran Ginosar

Goals

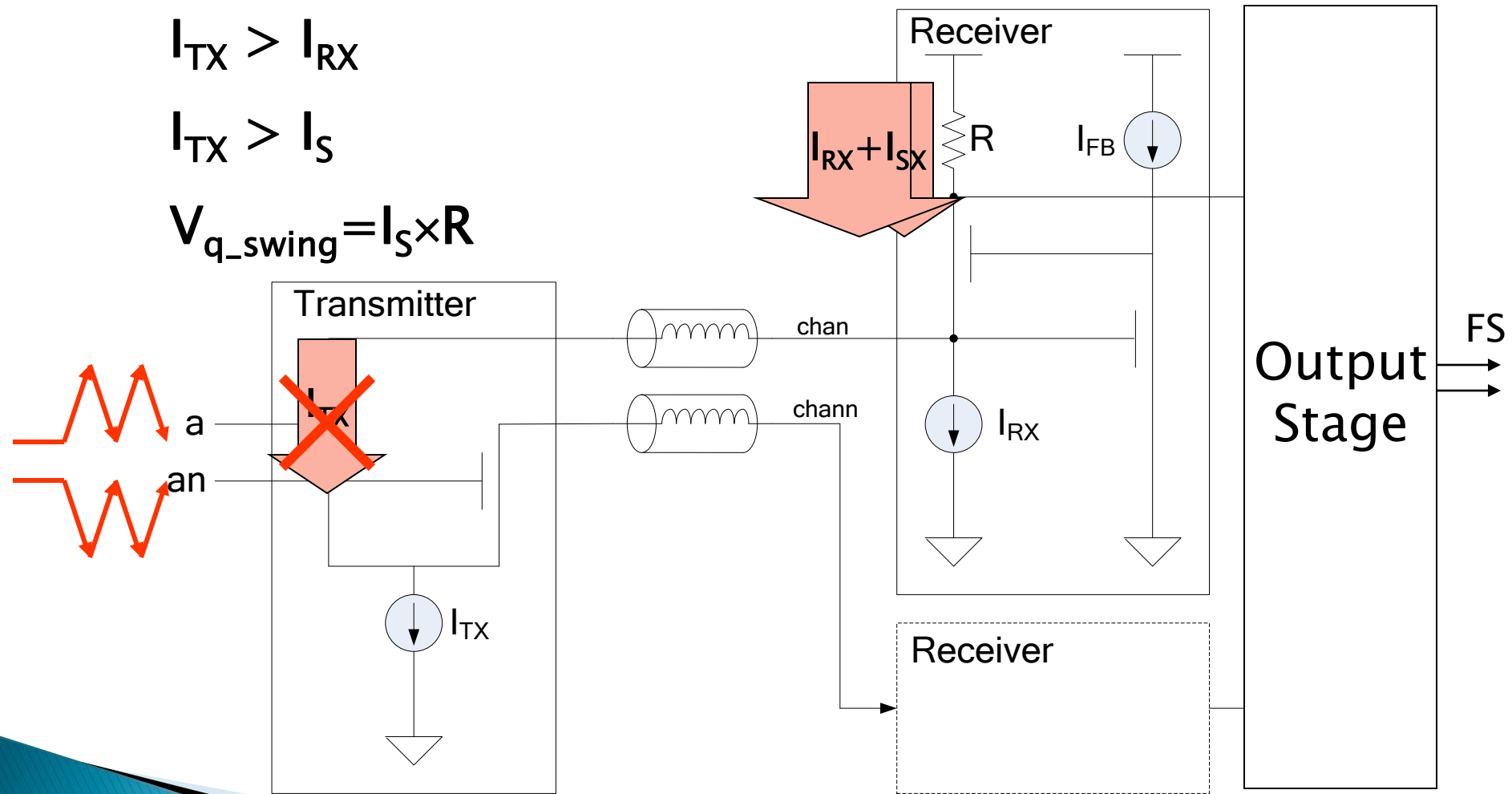
- ▶ Full Current Mode:
 - Send current from TX
 - Measure current at RX
- ▶ Minimal voltage swing over channel
- ▶ Current to voltage conversion at RX
- ▶ Long range repeater-less channel
- ▶ Targeted data cycle 15 ps (67 Gbps) @ 65nm
- ▶ Low power

Differential Channel Driver and Receiver

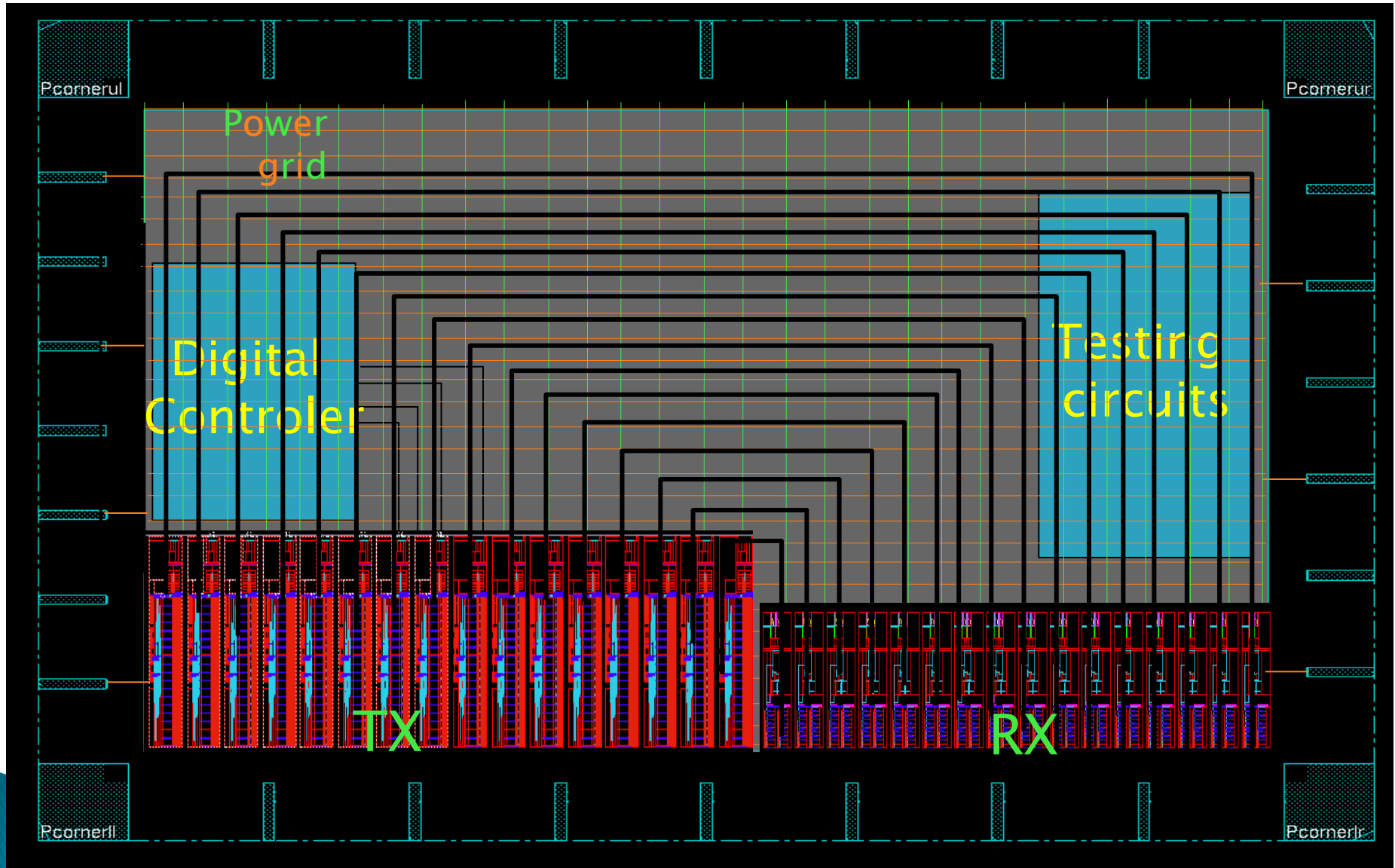
$$I_{TX} > I_{RX}$$

$$I_{TX} > I_S$$

$$V_{q_swing} = I_S \times R$$



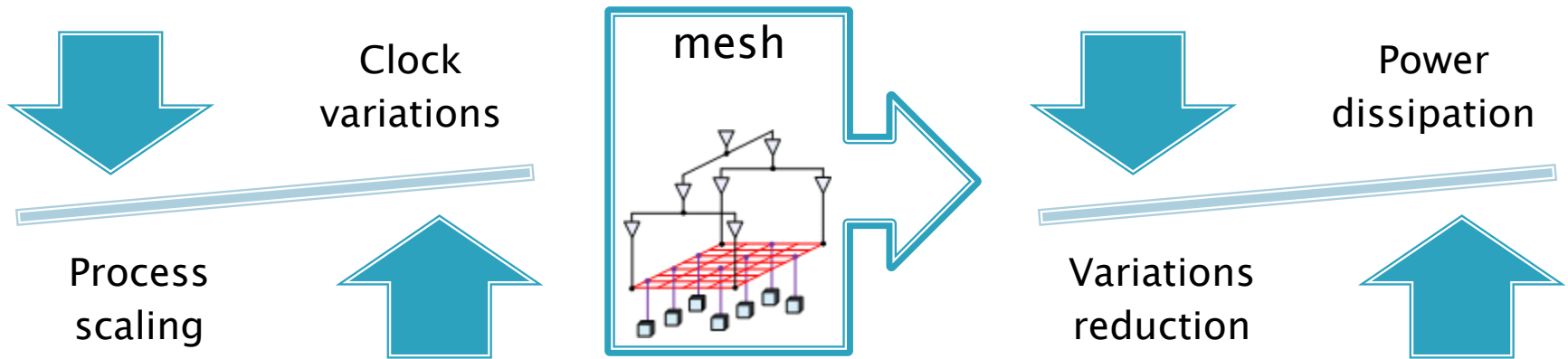
FOX chip structure



Timing-Driven Variation-Aware Nonuniform Clock Mesh Synthesis

Ameer Abdelhadi, Ran Ginosar, Avinoam Kolodny, and Eby G. Friedman

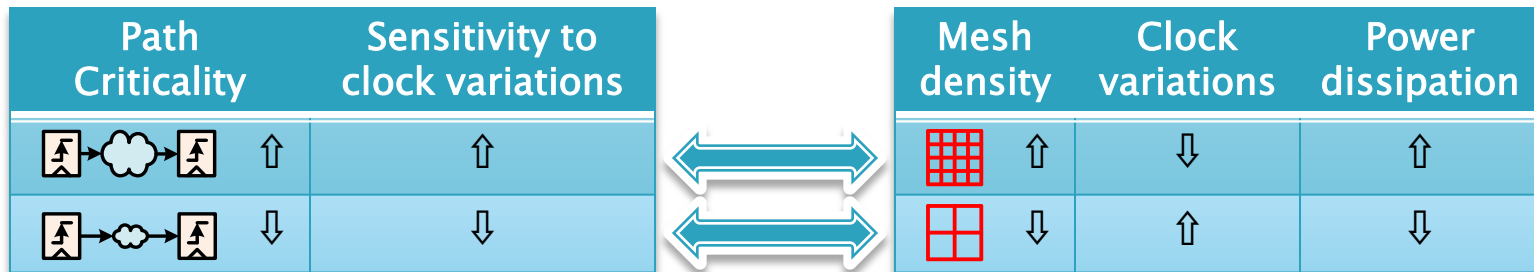
Motivation



Goal: reducing clock skew variations while keeping minimal power dissipation overhead

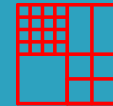
Timing-Driven Variation-Aware Nonuniform Clock Mesh Synthesis

Method



- Path criticality prioritization
- Managing skew tolerance

Nonuniform clock mesh

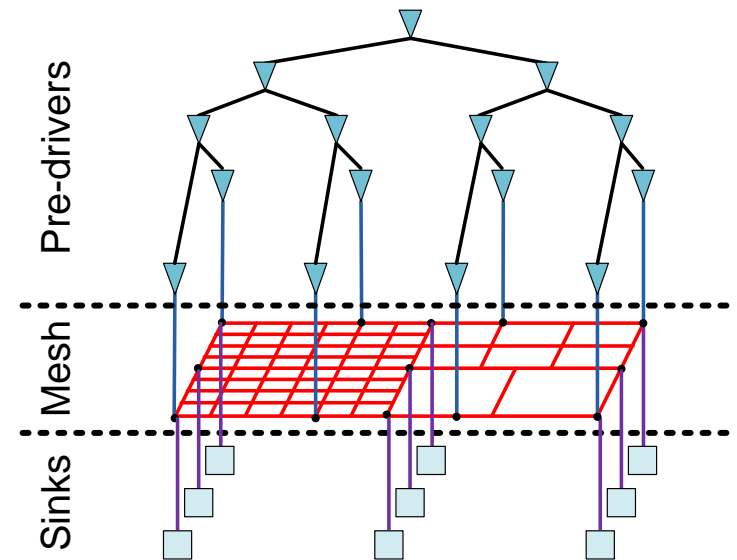
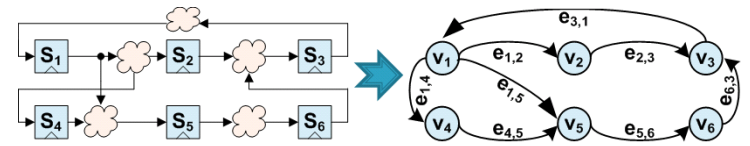


Selective reduction of clock skew variations based on circuit timing criticality

Timing-Driven Variation-Aware Nonuniform Clock Mesh Synthesis

Implementation

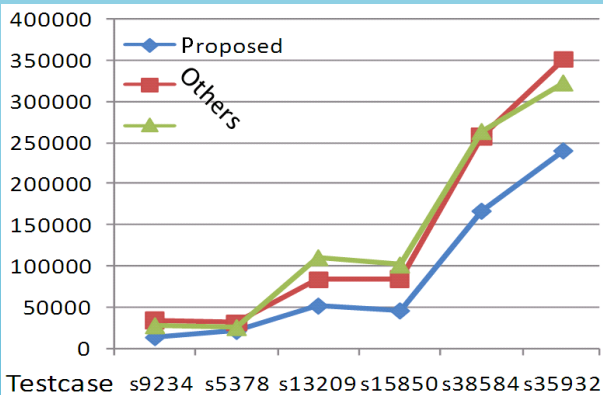
- ▶ Algorithms:
 - Graph-theoretic
 - for timing constraints
 - Geometric
 - for LO generation
- ▶ Quasi-linear ($n \log n$) runtime
- ▶ Design Environment:
 - RTL to layout design flow
 - Standard EDA tools
 - Standard 65nm library
 - ISCAS89 benchmarks



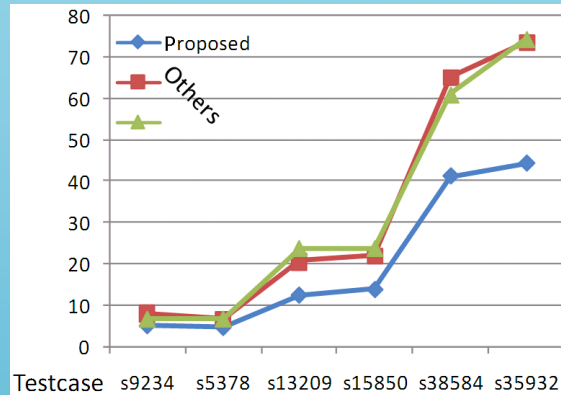
Timing-Driven Variation-Aware Nonuniform Clock Mesh Synthesis

Results

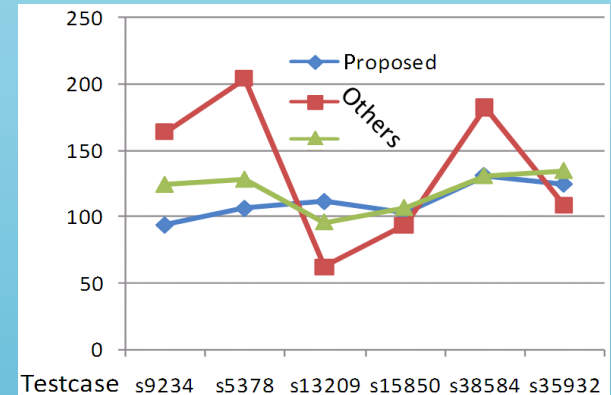
Wire length (um)



Power (mw)



Maximum skew (ps)

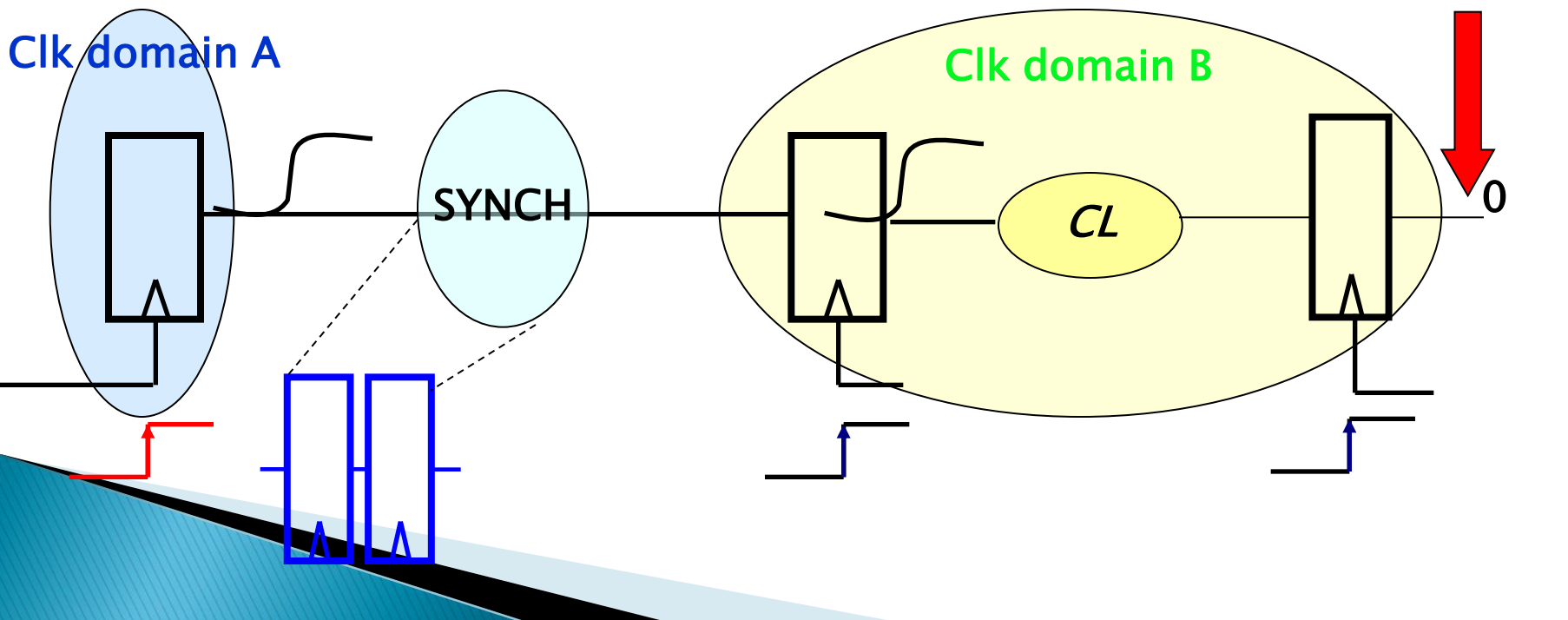


37% average reduction in metal
39% average reduction in power dissipation

Synchronizers degradation with scaling

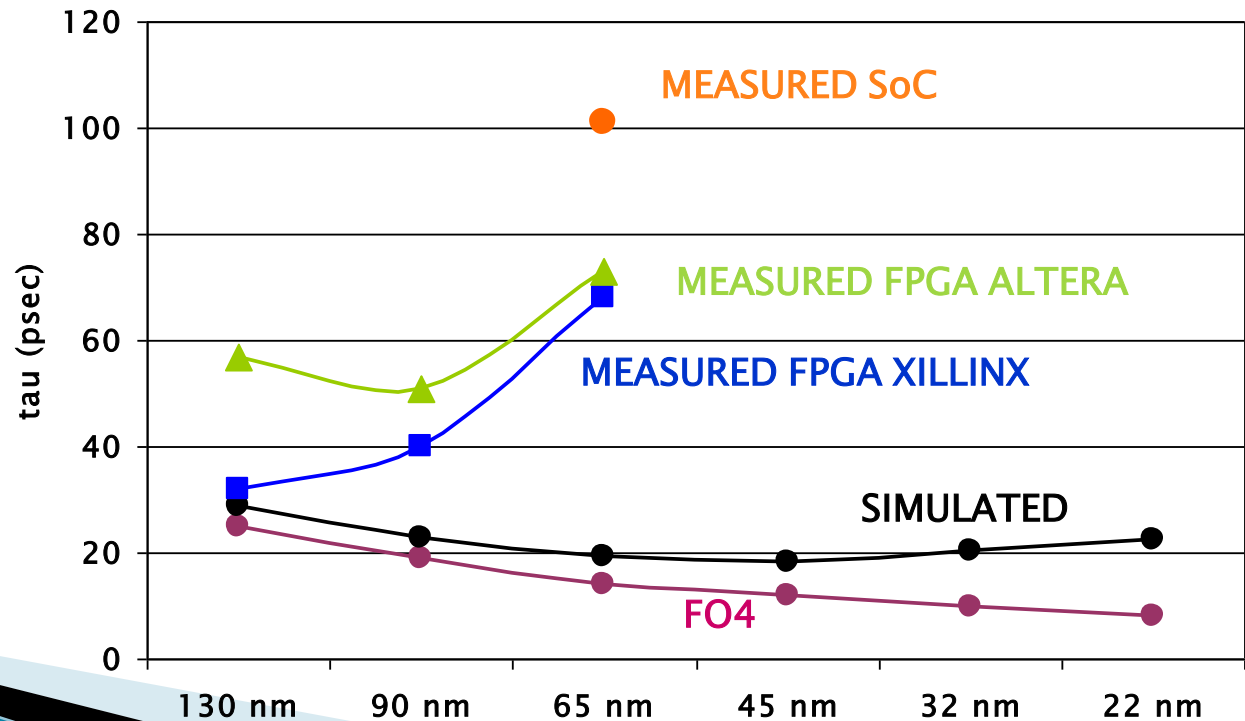
Shlomi Beer, Advisor: Prof. Ran Ginosar

- ▶ Circuits and SoCs employ multiple clock and voltage domains. Communication between different modules may lead to metastability.
- ▶ Metastability produces “esoteric” behavior in FF output. (increased delay)
- ▶ Metastability may lead to fatal errors.



Findings and Results

- ▶ Synchronizer performance is measured by its recovery time
 - Fast recovery → Good synch. Slow recovery → Bad synch
- ▶ Recovery time of synchronizers (τ) was believed to scale with technology.
- ▶ We found that τ degrades with scaling....



Research program for 2010

▶ Why ?

- Identify physical causes of the degradation effect

▶ How?

- Refine the metastability model

▶ Can we fix it?

- Develop circuits to mitigate the degradation effect

High performance computing in power and thermal constraint environment

Efi Rotem

Primary advisor: Ran Ginosar

Co advisors: Uri Weiser, Avi Mendelson

Masters work published at Micro-42

Continuing with PhD research



The power wall is here – call for action

$$\text{Power} = C * V^2 * F + \text{Leakage}$$

▶ Scaling of new Process technology:

- Linear Dimensions: Shrinks by 0.7
- Area: Shrinks by 0.7^2
- Capacitance: Shrinks by 0.7 (1.4X capacitance density)
- Frequency: Scale up by 1.4 (Lower scaling due to RC)
- Voltage: Scale down by 0.7 (Not scaling any more)



New process



New design



Traditionally – same power

Recent reality – higher power

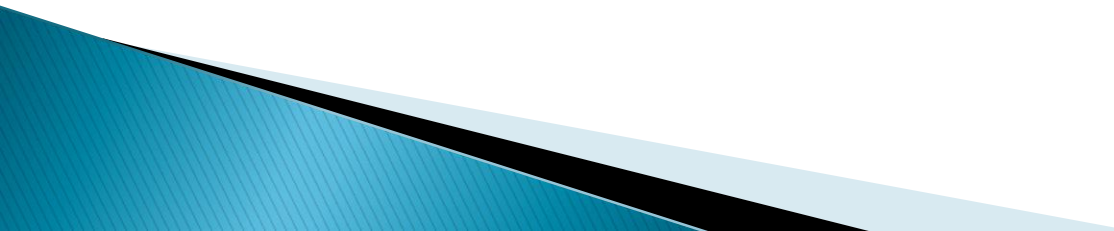
- **Industry is already in the power wall for almost a decade**
 - Continuously operating lower in the voltage range
 - Soon nominal voltage will equal min voltage

Compute performance roadmap is not sustainable any more

Other “Mega” Trends

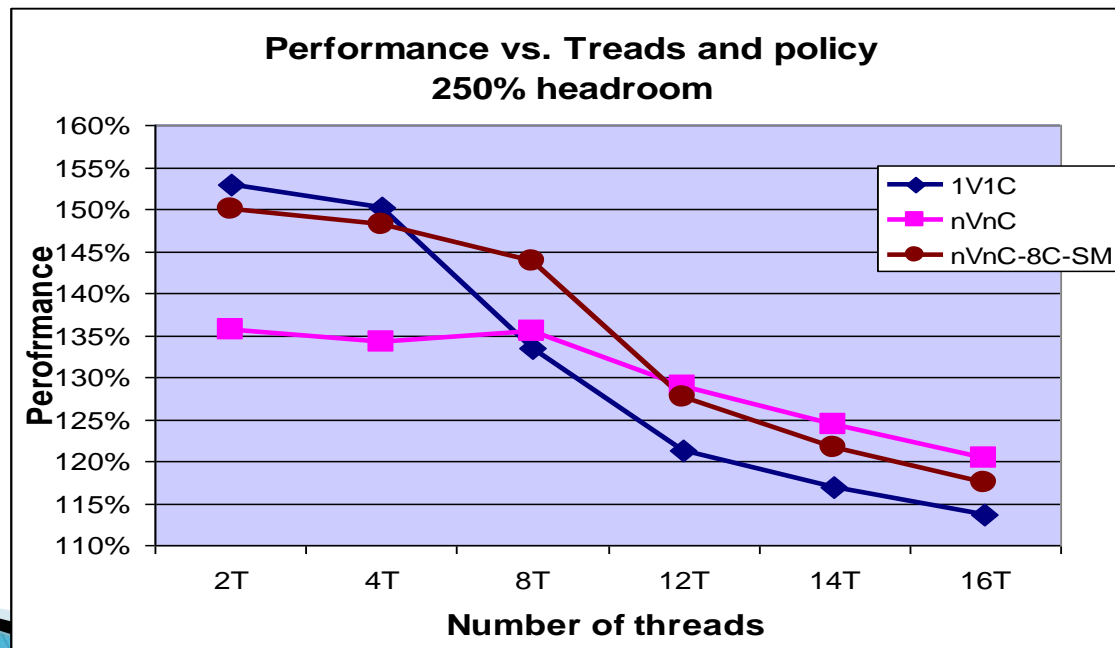
- ▶ Inside the chip:
 - Many cores – the dominant architecture
 - Migration of work to GP–GPU
 - Constraining physical parameters
 - Power, thermal, power delivery, process variability...
- ▶ Out of the chip:
 - The importance of power and energy in the data rack and the data center
- ▶ Resulting in increasing power and performance dynamic range
- ▶ The key for performance under physical constraints → Management

Our research directions

- ▶ How to best architect and manage a high performance CPU in order to:
 - ▶ Extract maximum performance within physical constraints
 - ▶ Optimize energy at performance constraints
- 

Micro-42 paper

- ▶ DVFS – A tool for power/perf. Management
- ▶ Introduced power delivery as a major constraint
 - Findings contradict some of previous studies
- ▶ Proposed clustered topology



Millimeter wave circuits and phase array systems in CMOS process

Emanuel Cohen

Supervisor : Dan Ritter

In cooperation with Intel



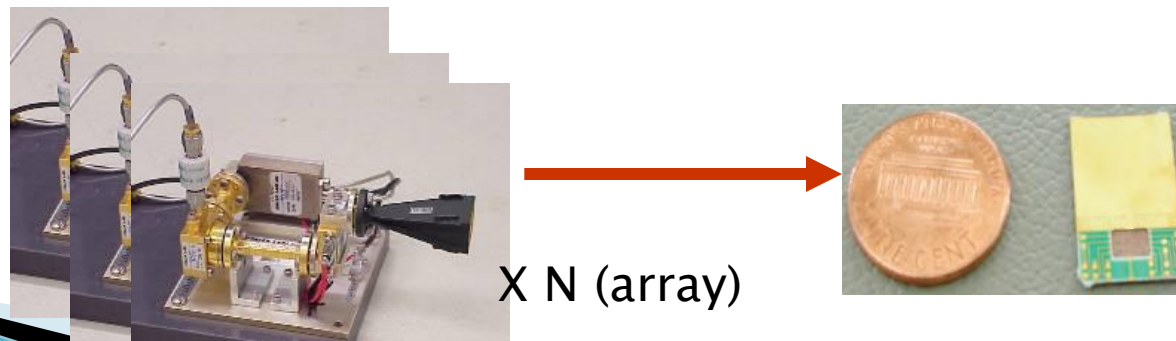
Goals and challenges of the research

Goals

- ▶ Design full phase array CMOS system in 60GHz – For $>5\text{Gb/s}$ data rate at $\sim 10\text{m}$ range with power consumption $< 1\text{Watt}$ size $< 20\text{mm}^2$
- ▶ Current circuit designs for mm-Wave result in power consumption greater than few Watts / size $> 100\text{mm}^2$, for $N > 30$ element array
- ▶ Analyze new architectural concepts and circuits design tradeoffs to meet power/size targets for mobile commercial application
- ▶ Examine innovative ways to benefit from CMOS integration and digital potential to create new systems in this area

Challenges

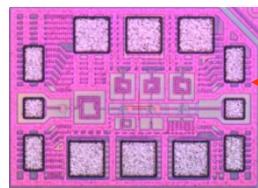
- ▶ Understand CMOS process advantages and limitations for mm wave use
- ▶ Circuit design at high freq close to F_{max} raises many research challenges on topologies and system performance



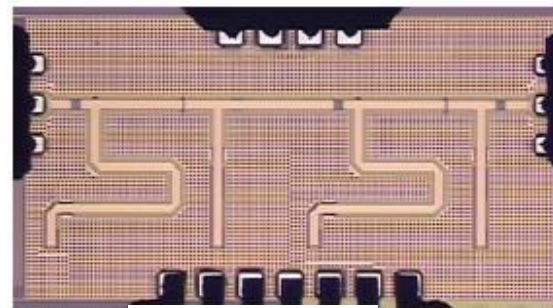
Create the basics for small low power fully integrated phase array system

First research step (completed)

- ▶ Analysis of a phase array system – **understand the limitations for the smallest and most efficient system possible.**
- ▶ Flow definition for design and models for the basic passives and transistors in CMOS mm
- ▶ Design building blocks : LNA, PA, switches, phase shifters, mixers and combiners
- ▶ Design arrays : 4 element array, 32 element array + bump transition simulations and test structures
- ▶ Test measurement and investigation of all blocks



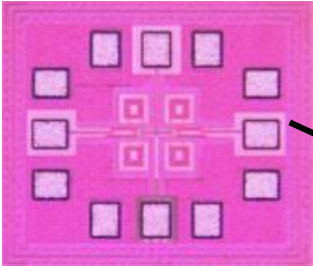
Inductor design



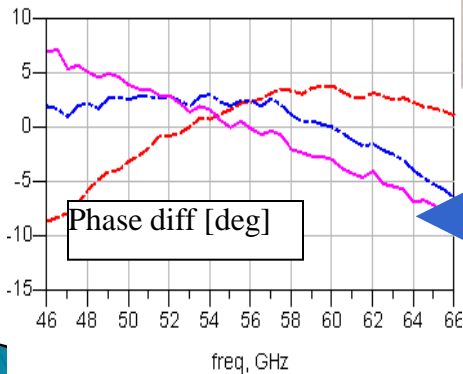
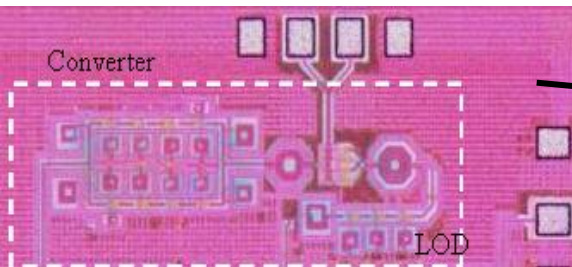
TL design

Circuits design

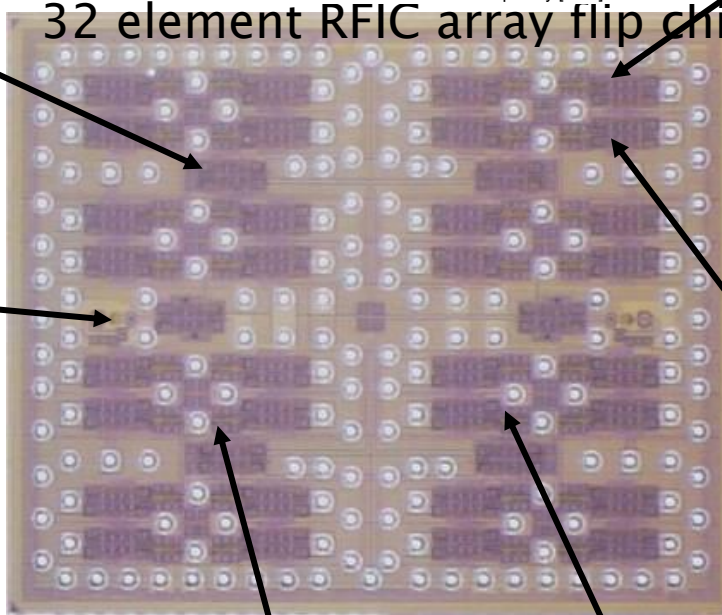
Combiner



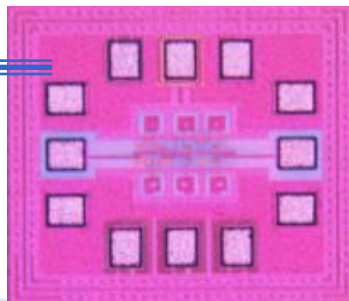
Mixer + LO drive



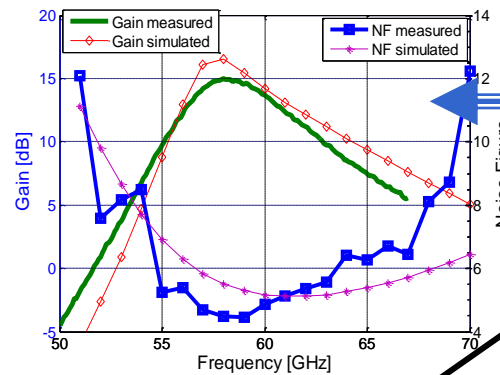
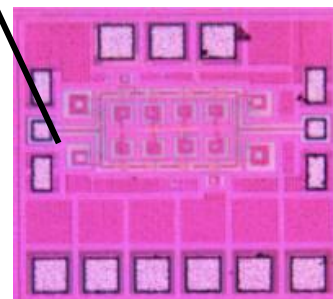
32 element RFIC array flip chip



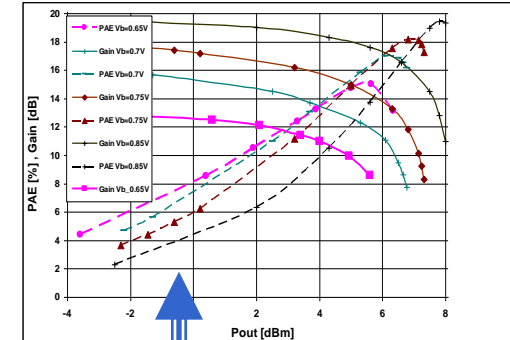
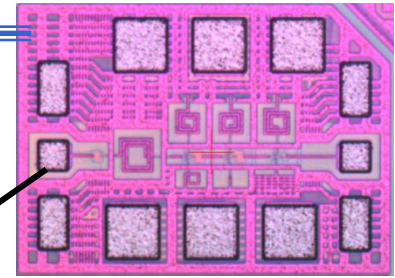
Phase shifter



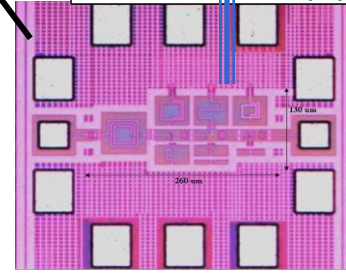
LNA with PA and Switch



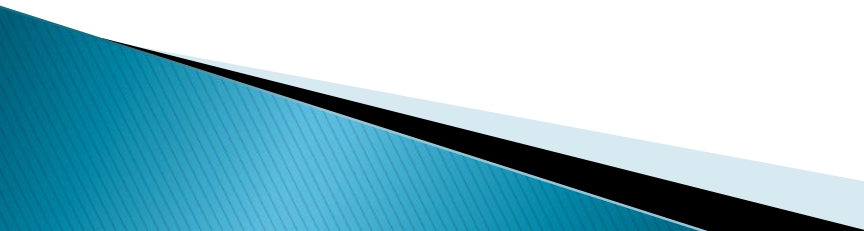
LNA



PA



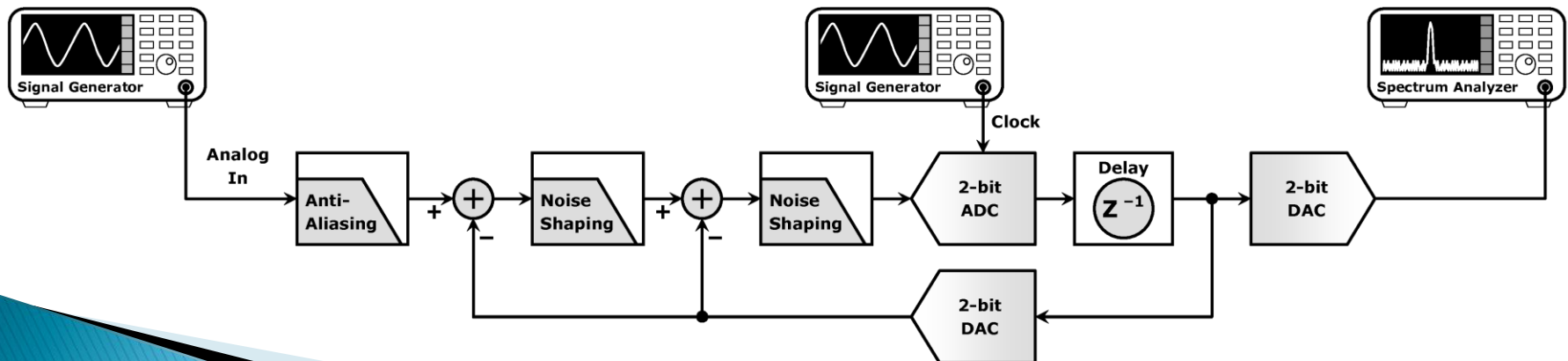
Next steps

- ▶ Focus on fundamental design issues of the circuits and the full system – based on array data
 - ▶ System level mismatch impact
 - ▶ Element coupling in array
 - ▶ Circuit level limitations: passive switching and amplifier gain boosting vs. bandwidth
 - ▶ Integration of antenna for phase array inside the silicon, and create a very compact system
- 

Building Blocks for High Speed $\Delta\Sigma$ ADC in InP HBT Technology

Shraga Kraus, Supervised by Dan Ritter

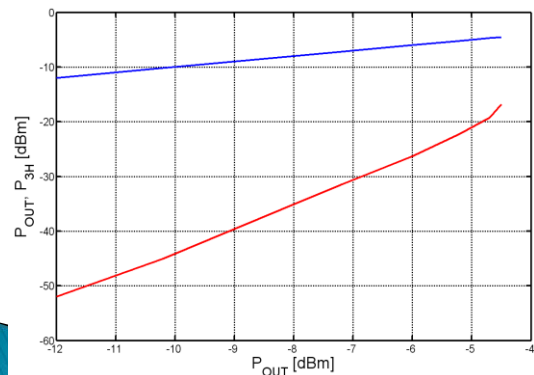
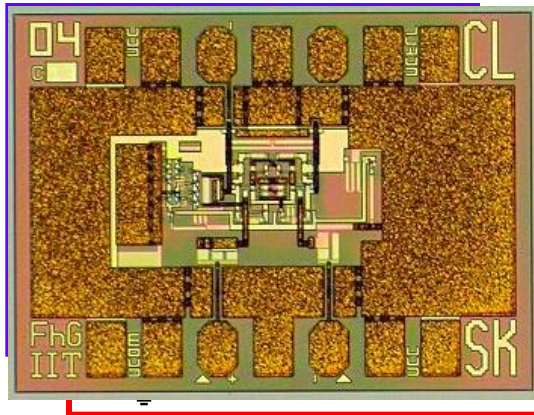
- ▶ Goal: develop analog circuit technology to enable multi-bit $\Delta\Sigma$ ADC in HBT
- ▶ Stage 1: Building blocks
- ▶ Stage 2: Complete ADC



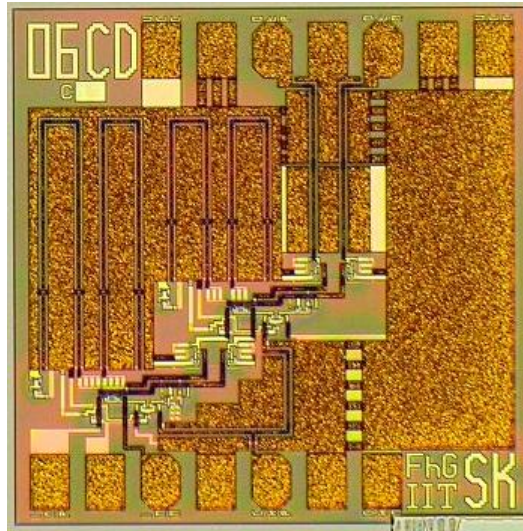
Summary

▶ Building blocks:

▶ High-gain op amp:

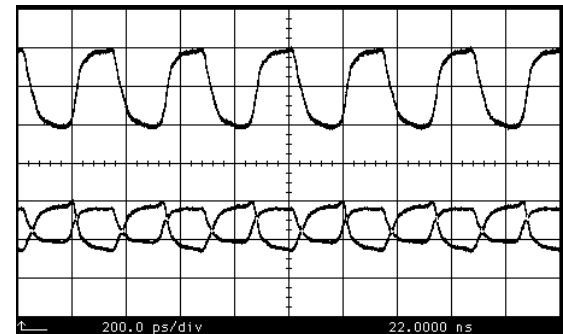
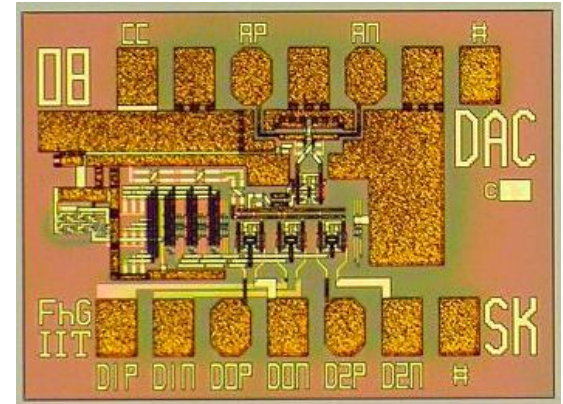


▶ Latched comparator:



Sensitivity (@20 GHz) improves:
17 mV → 10 mV

▶ 2-bit DAC:

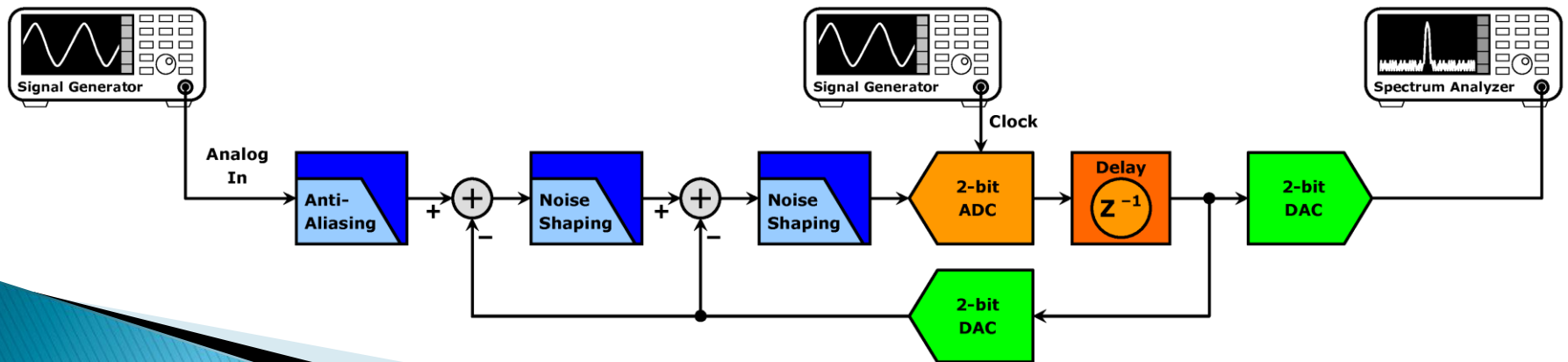


f1 50.0 mV/div -99.8 mV
3 50.0 mV/div 93.4 mV
4 50.0 mV/div 87.0 mV

Summary

- ▶ Building blocks:
 - ▶ High-gain op amp
 - ▶ Latched comparator
 - ▶ 2-bit DAC

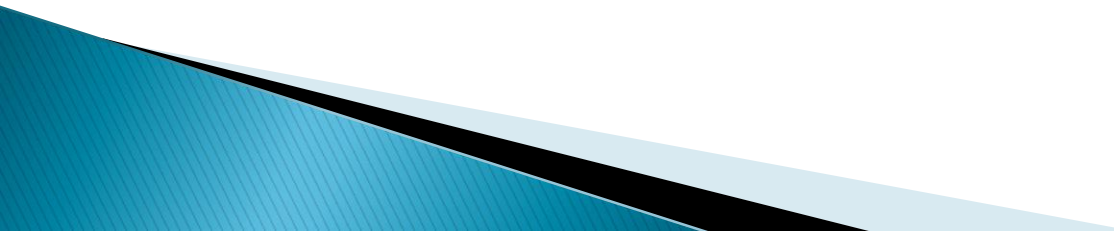
- ▶ Complete ADC



A dark, arched stone tunnel with a metal gate at the end, leading to a bright light. The tunnel is made of rough-hewn stone and is dimly lit, with the light coming from the opening at the end. A metal gate with a grid pattern is partially open, revealing a bright, overexposed area beyond. The text "The End" is centered in the middle of the tunnel.

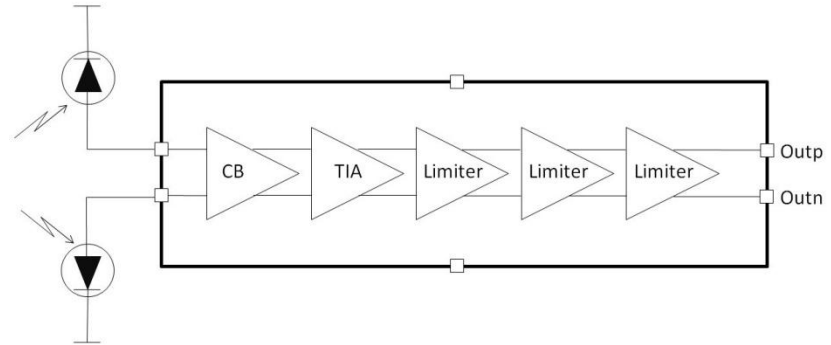
The
End

A 40Gbs differential TIA using InP HBT Technology, Eli Bloch and Prof. Dan Ritter

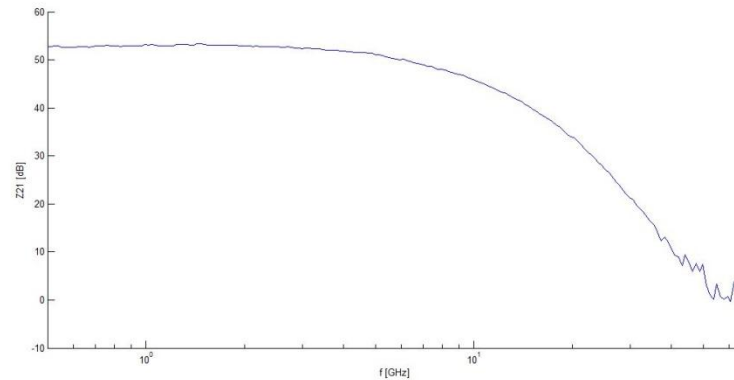
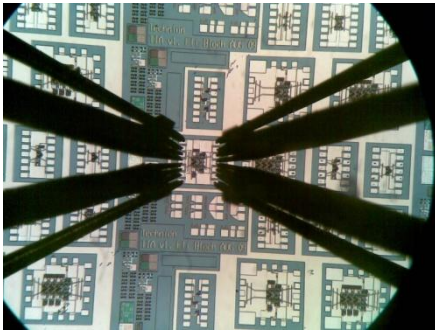
- ▶ 40GHz BW
 - ▶ 2K Ω Transimpedance gain
 - ▶ Large and small signal combination
 - ▶ High input dynamic range
 - ▶ Output limiting
 - ▶ Low BER
 - ▶ Single device modeling, process optimization and measurements.
- 

A 40Gbs differential TIA using InP HBT Technology

► Building Blocks



► Results:



Macro Models for Power at RT Level

Anna Kouslik

under supervision of Assoc. Prof. Avinoam Kolodny

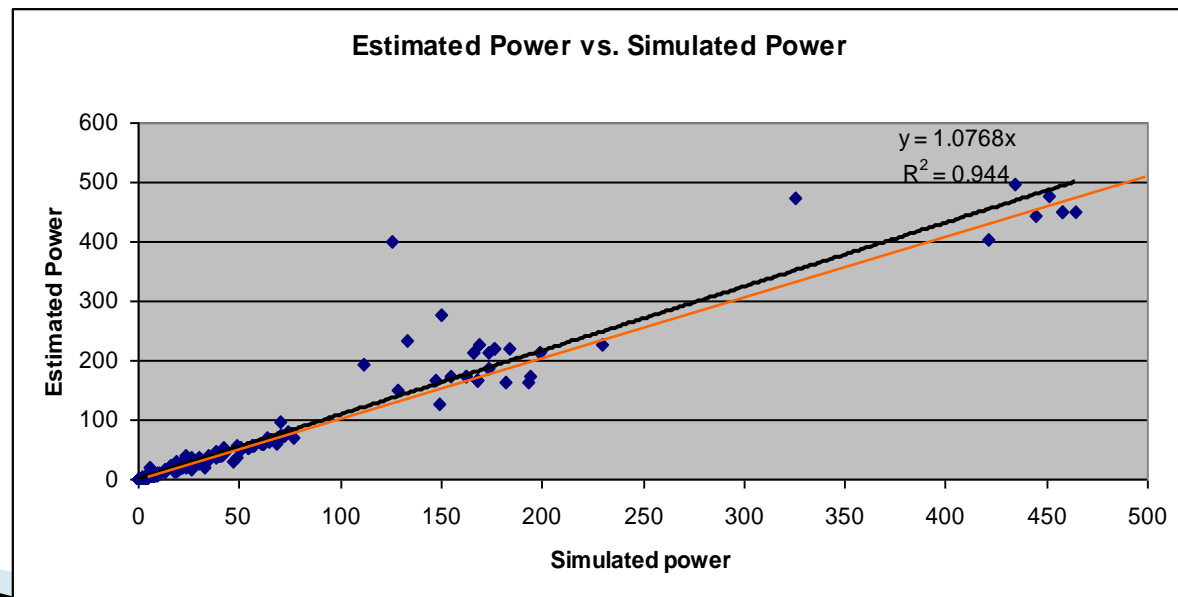
- ▶ **Goal:** provide accurate schematic–annotated model for power estimation at RTL allowing
 - Fast feedback to RTL designer on incremental changes
 - Running long and numerous workloads for uArch/RTL analysis
- ▶ **Challenges:**
 - Generating *generic* model working for all type of circuits
 - Most of academia research focused on combinatorial circuits
 - Generating *physical* model
 - Which can be used for what–if analysis for incremental RTL changes

Macro Models for Power at RT Level

- ▶ Statistical approach based on ‘mapping for power’
 - For each RTL signal identify sub-circuit it is responsible for
 - Assign effective capacitance to each RTL signal derived from its respective sub-circuit
 - Estimate power at RTL by:

$$P_{dyn} = 0.5V^2 f \sum_{\text{all RTL nodes } r} C_r^{eff} \cdot \alpha_r$$

- ▶ Accuracy results on 400 tests:



Finding the Energy Efficient Curve:

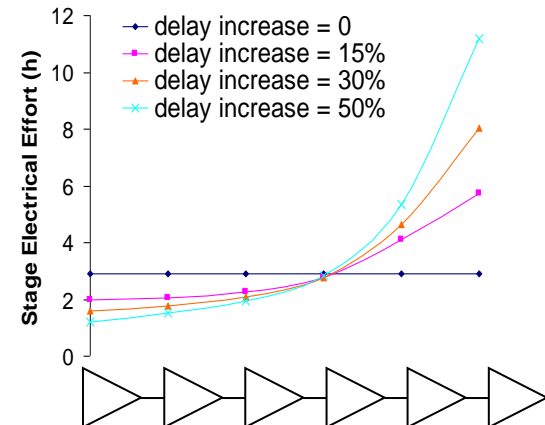
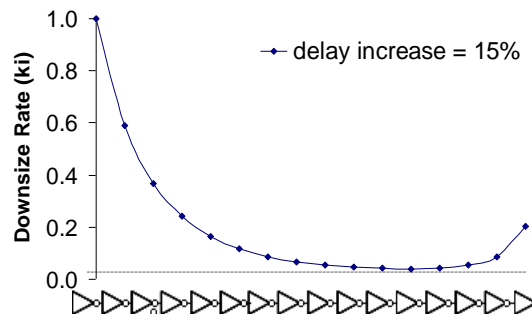
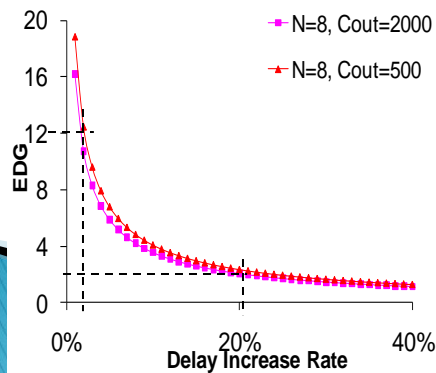
Gate Sizing for Minimum Power under Delay Constraints

Yoni Aizik and Avinoam Kolodny

- ▶ Main challenge: reduce switching power of a CMOS design in an optimal way, by gate resizing.
 - How to downsize the gates, to gain maximum power savings, and minimum affect on timing?
 - Answer the questions:
 - How much energy can be saved by slowing down the circuit by x percent?
 - How to determine gate sizes for optimal power under a given delay constraint?
 - How to downsize the gates, to gain maximum power savings, and minimum affect on timing? Uniformly?

Solution

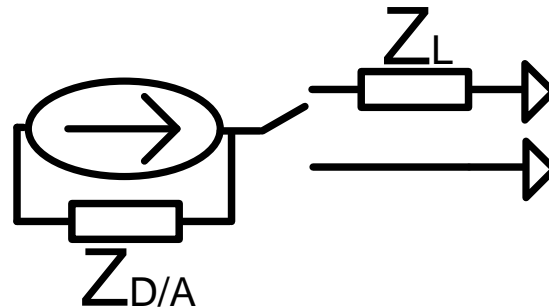
- ▶ Build logical effort model of the circuit
- ▶ Solve the (convex) optimization problem:
 - For a given circuit, with initial sizing, AF, and required performance degradation, find new sizing that maximizes energy reduction.
- ▶ We wrote a tool written over Matlab that solves the optimization problem for a given circuit



Low Power D/A Converter Design Considerations – Y.Cohen A.Unikovski

- ▶ Current steering D/A converter
 - Single ended operation – poor power efficiency
 - Dynamic range is limited by load and output impedance ratio

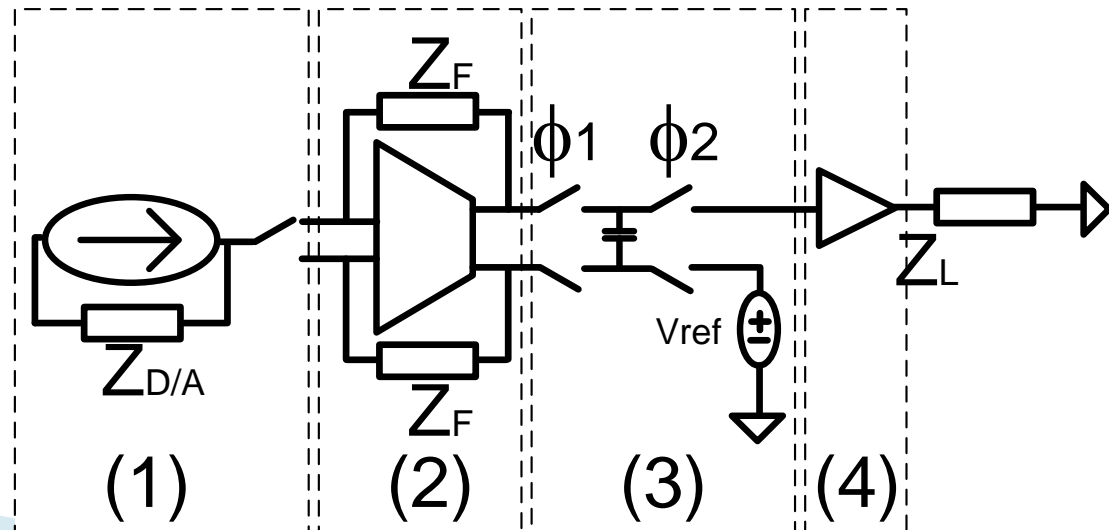
$$Z_{D/A}/Z_L \uparrow \rightarrow DR \uparrow$$



- ▶ The Goal of this research is to improve the power efficiency of the D/A conversion system

Low Power D/A Converter Design Considerations

- ▶ This work
 - Low power Differential output D/A converter – 0.2mA full scale current (1)
 - Trans-impedance amplifier as the D/A load – improve dynamic range (2)
 - Differential to single ended conversion using switch capacitor architecture (3)
 - Output buffer with impedance matching (4)

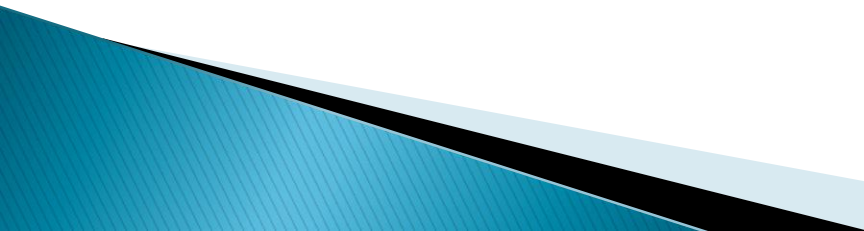


On-die Power Network Optimization

Michael Sotman (supervisors: E. Friedman, A. Kolodny)

- ▶ Goal: provide recommendations for on-die power delivery network optimization
- ▶ Challenges:
 - Wide current consumption spectrum
 - Multiple voltage domains
 - Lack of on-die decoupling
 - Effective interaction with package
 - Adaptation of power network for on-die power gating and/or on-die voltage regulator

On-die Power Network Optimization

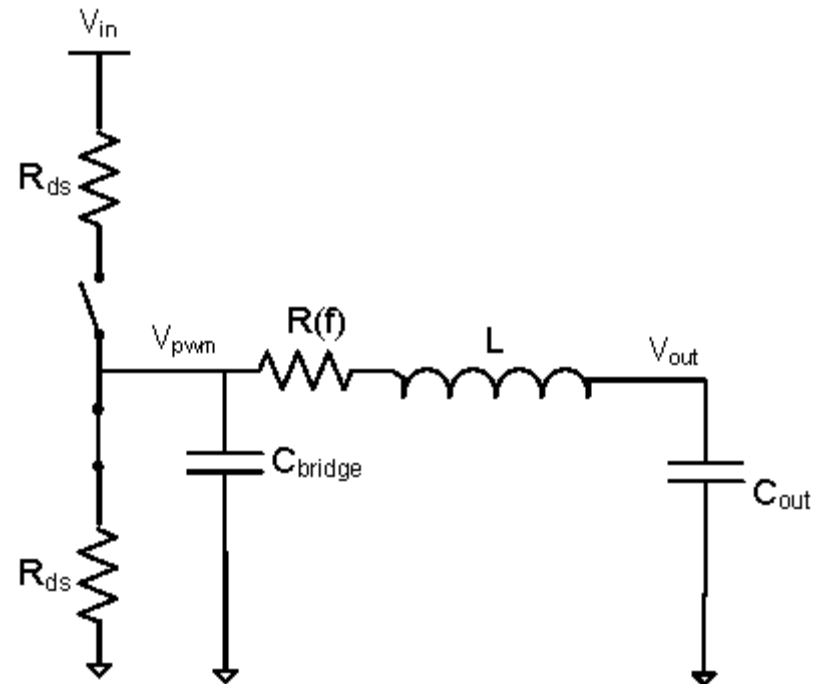
- ▶ Approach: analysis in frequency domain as well as in time domain
 - ▶ Results: TBD
 - ▶ Research program for 2010:
 - Development of idea of parallel routing in adjacent metal layers
 - Analysis of C4 bump effective radius
 - Analysis of recharge influence of on-die decoupling effectiveness
- 

On-chip DC-DC buck converter

Presenter: Gregory Sizikov

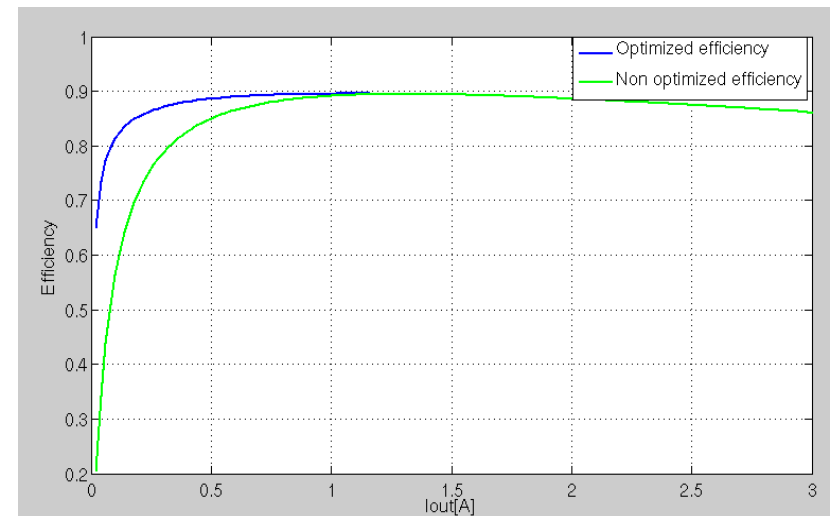
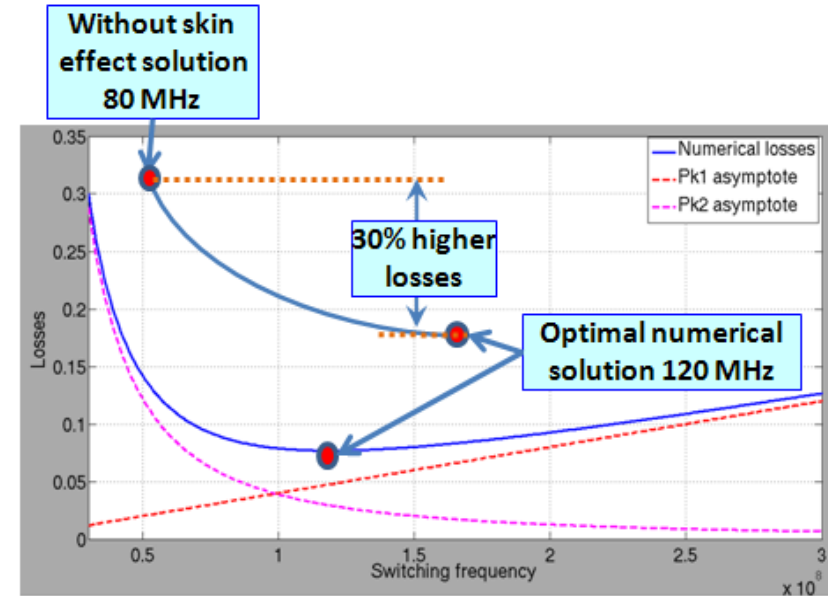
Advisors: E. Friedman, Avinoam Kolodny, Michael Zelikson

- ▶ The goal of the research is to discuss performance aspects of DC-DC switching buck converter integration
- ▶ Integration challenges:
 - Smaller power path components (LC filter)
 - High switching frequency
 - Sub um process design



On-chip DC-DC buck converter

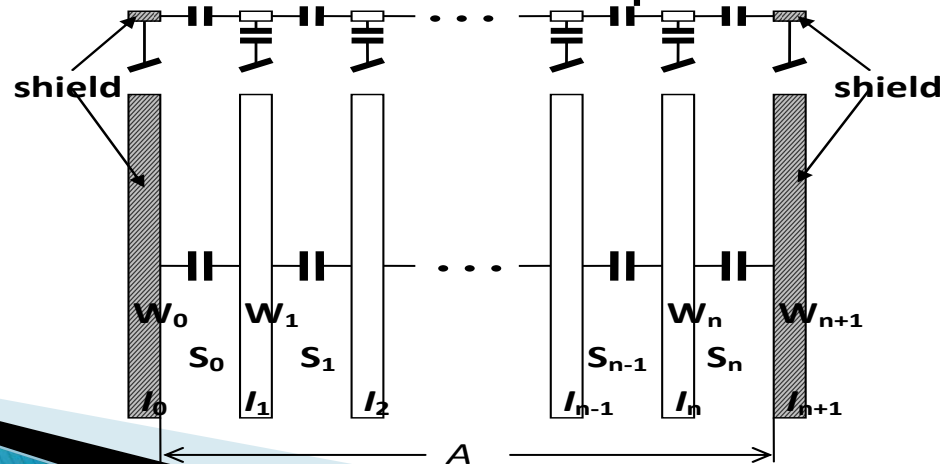
- ▶ The approach taken:
 - Develop analytic expressions for integrated DC-DC converter efficiency, extract their parameters, and validate vs full circuit simulation
 - ▶ Results:
 - Optimal switching frequency found
 - Light load optimization performed
 - ▶ Research program for 2010
 - Expand the optimization to high load current dynamic range
- Publish the results



Interconnect power optimization under gridded design rules (1)

Konstantin Moiseev (supervisors: S. Wimer, A. Kolodny)

- ▶ Interconnect power is important component of total dynamic power (~50%)
- ▶ The lithography used for 32 nanometers and smaller VLSI process technologies restricts the admissible interconnect widths and spaces to a small set of discrete values
- ▶ The idea: represent size allocation of wires in interconnect channel as a sequential decision problem



Interconnect power optimization under gridded design rules (2)

- ▶ The problem was shown to be NP-complete
- ▶ DP programming algorithm solving the problem has been developed and implemented
 - The algorithm can handle various combinations of power and delay (i.e. sum power – sum delay, sum power – max delay etc.)
- ▶ Pareto (non-redundant) power–delay curve is generated as a result of algorithm work
 - The designer can choose desired solution according to given power (delay) envelope
- ▶ We showed that that 5 values of available wire widths and spaces are enough to get to as close as 5% from the exact continuous solution and that using just two or three values of widths and spaces is insufficient
- ▶ The application of the algorithm on real design blocks showed reduction of 18% in interconnect power and 9% in interconnect delay on average

